

**600V N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

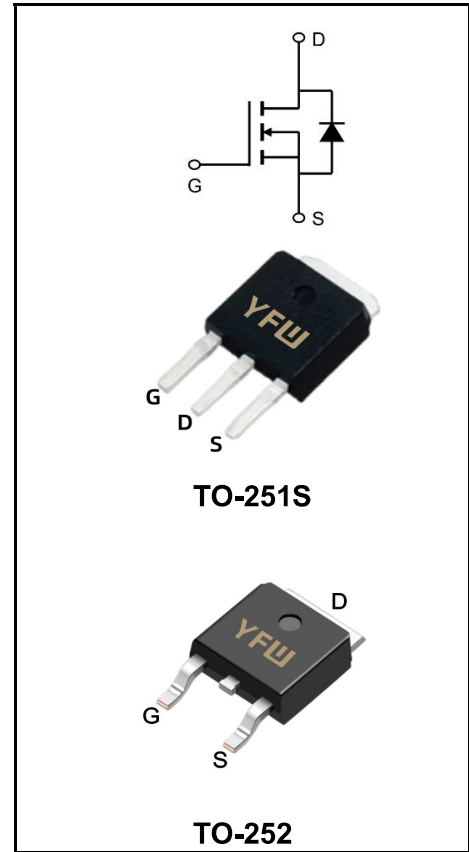
<b>I<sub>D</sub></b>	2A
<b>V<sub>DSS</sub></b>	600V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	<4.2Ω( <b>Type:3.5 Ω</b> )

**Features**

- ◆Fast Switching
- ◆Low ON Resistance
- ◆Low Gate Charge
- ◆100% Single Pulse avalanche energy Test
- ◆LeadfreeincomplywithEURoHS2011/65/EUdirectives

**Mechanical Data**

- ◆Case: Molded plastic
- ◆Mounting Position: Any
- ◆Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆Solder bath temperature275°C maximum,10s per JESD22-106



**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
		251/252	
Drain-Source Voltage	<b>V<sub>DS</sub></b>	600	<b>V</b>
Gate-Source Voltage	<b>V<sub>GS</sub></b>	±30	<b>V</b>
Continue Drain Current	<b>I<sub>D</sub></b>	2	<b>A</b>
		- Continuous(Tc=100°C)	
Pulsed Drain Current (Note1)	<b>I<sub>DM</sub></b>	8	<b>A</b>
Power Dissipation	<b>P<sub>D</sub></b>	35	<b>W</b>
		-Derate above 25°C	
Single Pulse Avalanche Energy (Note2)	<b>E<sub>AS</sub></b>	55	<b>m<sub>J</sub></b>
Avalanche Current (Note 1)	<b>I<sub>AR</sub></b>	2	<b>A</b>
Repetitive Avalanche Energy (Note 1)	<b>E<sub>AR</sub></b>	3.2	<b>m<sub>J</sub></b>
Operating Temperature Range	<b>T<sub>J</sub></b>	150	<b>°C</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to +150	<b>°C</b>
Thermal Resistance, Junction to Case	<b>R<sub>θJC</sub></b>	3.57	<b>°C/W</b>
Thermal Resistance, Junction to Ambient	<b>R<sub>θJA</sub></b>	62.5	<b>°C/W</b>

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	<b>BV<sub>DSS</sub></b>	600	-	-	<b>V</b>
Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ (Referenced to 25°C)	$\frac{\Delta BVDSS}{\Delta T_J}$	-	0.65	-	<b>V/°C</b>
Drain-Source Leakage Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	<b>I<sub>DSS</sub></b>	-	-	1	<b>uA</b>
	$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$		-	-	10	<b>uA</b>
Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	<b>I<sub>GSS</sub></b>	-	-	±100	<b>nA</b>
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	<b>V<sub>GS(th)</sub></b>	2	-	4	<b>V</b>
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 1\text{ A}$	<b>R<sub>DS(on)</sub></b>	-	3.5	4.2	<b>Ω</b>
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 1\text{ A}$	<b>g<sub>fs</sub></b>	-	1.8	-	<b>S</b>
Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	<b>C<sub>iss</sub></b>	-	310	-	<b>pF</b>
Output Capacitance		<b>C<sub>oss</sub></b>	-	32	-	
Reverse Transfer Capacitance		<b>C<sub>rss</sub></b>	-	6	-	
Turn-on Delay Time	$I_D = 2\text{ A}, V_{DD} = 300\text{ V}, R_G = 10\ \Omega$ (Note3,4)	<b>td(ON)</b>	-	8	-	<b>nS</b>
Rise Time		<b>tr</b>	-	6	-	
Turn-Off Delay Time		<b>td(OFF)</b>	-	30	-	
Fall Time		<b>tf</b>	-	11	-	
Total Gate Charge	$I_D = 2\text{ A}, V_{DD} = 300\text{ V}, V_{GS} = 10\text{ V}$ (Note3,4)	<b>Q<sub>G</sub></b>	-	8	-	<b>nC</b>
Gate to Source Charge		<b>Q<sub>GS</sub></b>	-	1.5	-	
Gate to Drain Charge		<b>Q<sub>GD</sub></b>	-	4	-	

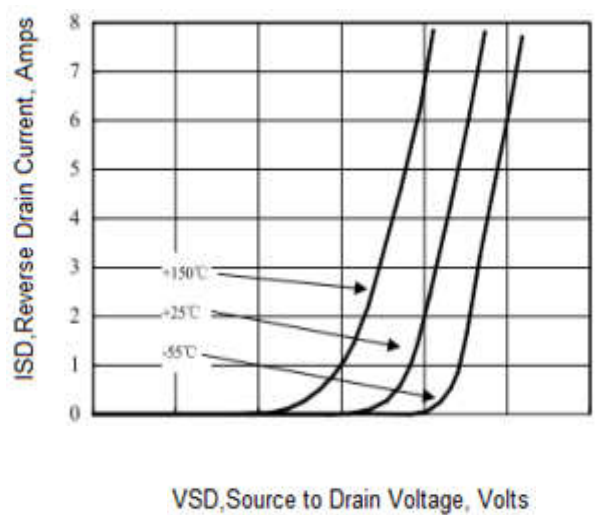
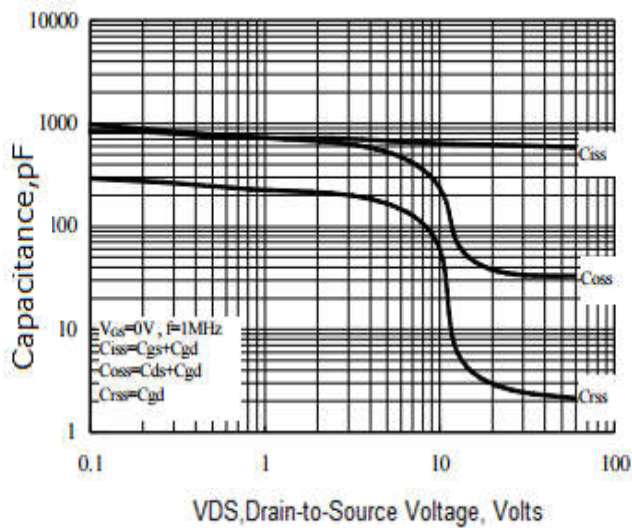
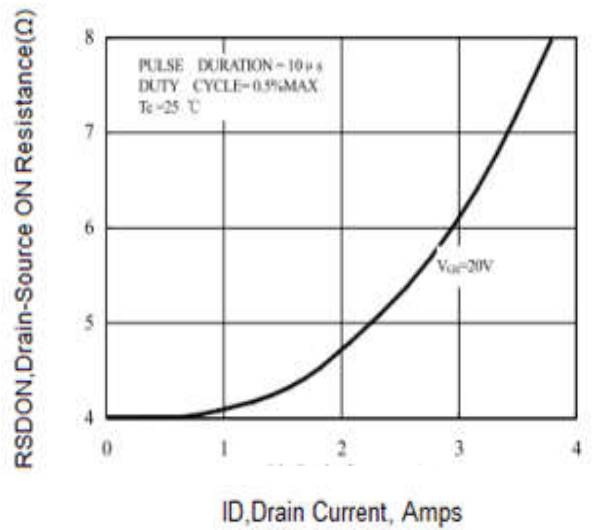
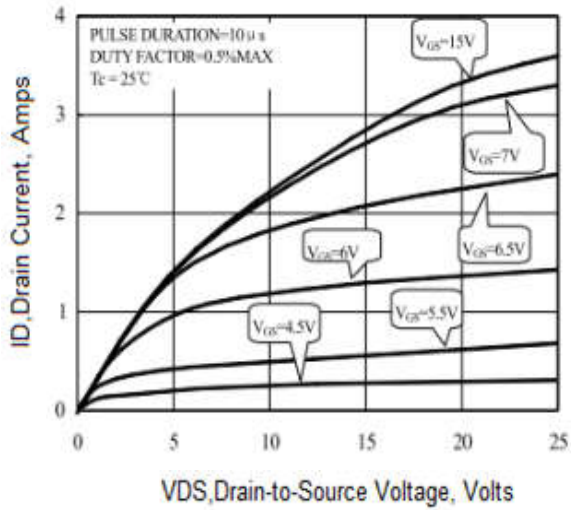
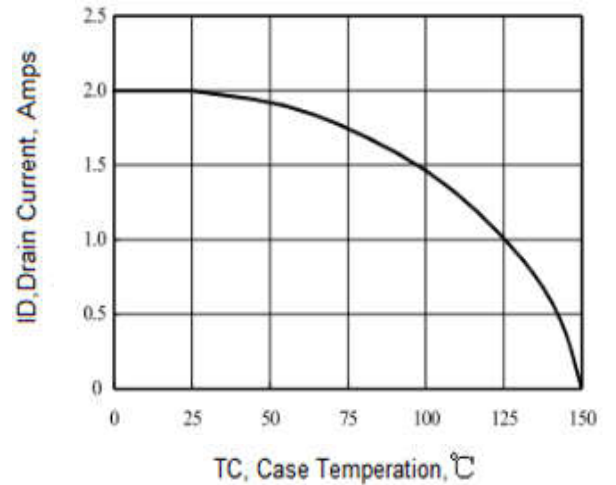
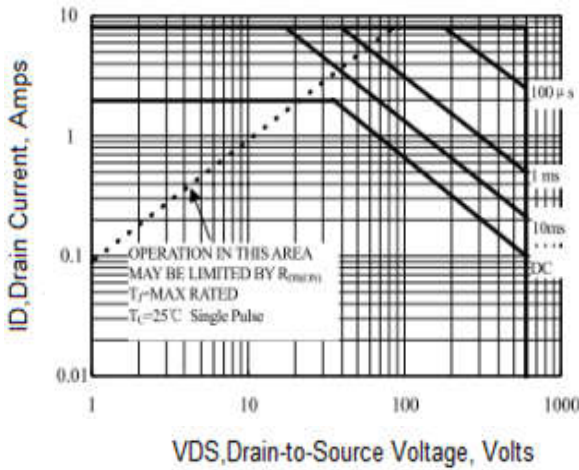
**Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified**

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximun Body-Diode Continuous Current		<b>I<sub>S</sub></b>	-	-	2	<b>A</b>
Maximun Body-Diode Pulsed Current		<b>I<sub>SM</sub></b>	-	-	8	<b>A</b>
Drain-Source Diode Forward Voltage	$I_{SD} = 2\text{ A}$	<b>V<sub>SD</sub></b>	-	-	1.4	<b>V</b>
Reverse Recovery Time	$I_{SD} = 2\text{ A}, V_{GS} = 0\text{ V}, dI_F / dt = 100\text{ A}/\mu\text{s}$	<b>trr</b>	-	410	-	<b>nS</b>
Reverse Recovery Charge		<b>Q<sub>rr</sub></b>	-	1.2	-	<b>uC</b>

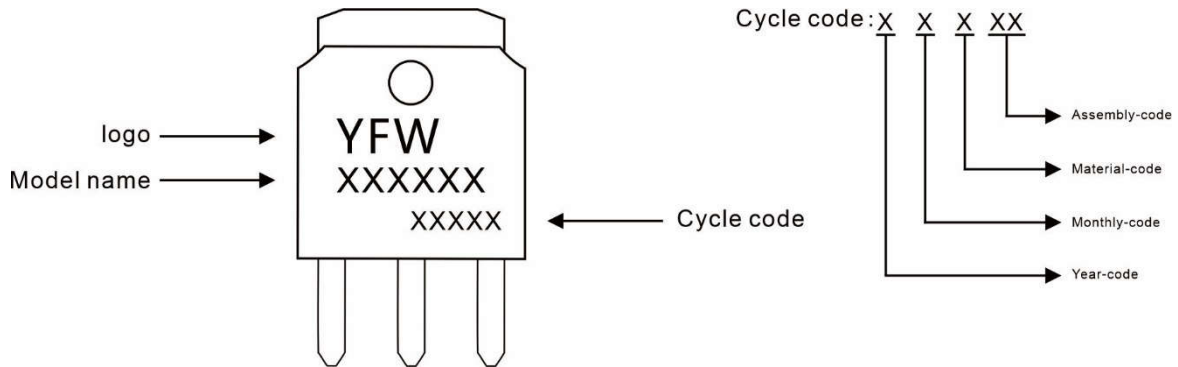
Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. IAS = 2 A, VDD = 50 V, L = 28mH, RG = 25Ω, starting TJ = 25°C.
3. ulse test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
4. Essentially Independent of Operating Temperature.

Ratings and Characteristic Curves



**Marking Diagram**



**Ordering information**

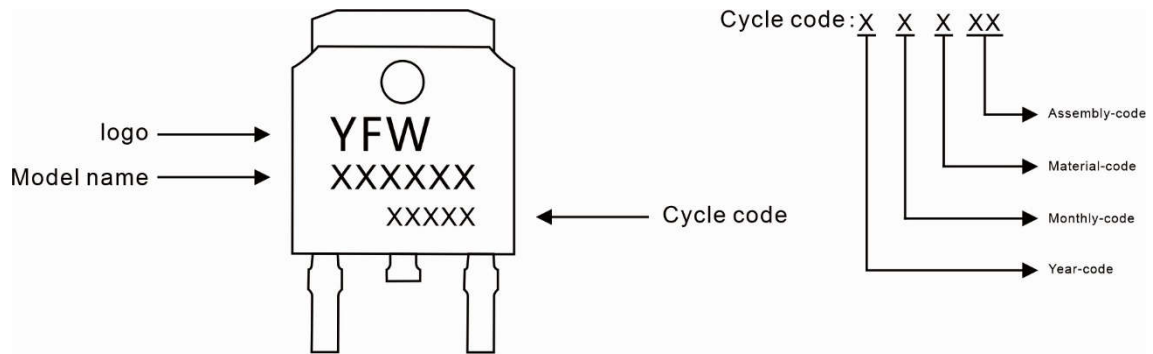
Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW2N60AMJ	TO-251S	0.011oz(0.32g)	80pcs/tube	4000pcs/box 24000pcs/Carton

**Package Dimensions**

**TO-251S**

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.1	2.5	0.083	0.098
A1	6.3	6.9	0.248	0.271
A2	0.9	1.1	0.035	0.043
A3	TYP0.5		TYP0.019	
b	0.6	0.8	0.024	0.031
c	0.4	0.5	0.015	0.020
D	5.3	5.5	0.209	0.217
D2	3.65	4.05	0.144	0.159
E	5.8	6.4	0.228	0.252
E2	0.9	1.4	0.035	0.055
e	TYP2.29		TYP0.090	
e1	TYP4.58		TYP0.180	
L	3.7	4.3	0.146	0.169

**Marking Diagram**



**Ordering information**

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW2N60AD	TO-252	0.011oz(0.32g)	2500pcs/reel	5000pcs/box 25000pcs/Carton

**Package Dimensions**

**TO-252**

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.50	0.087	0.098
A1	0.00	0.12	0.000	0.005
A2	2.20	2.40	0.087	0.094
B	1.20	1.60	0.047	0.063
b	0.50	0.70	0.020	0.028
b1	0.70	0.90	0.028	0.035
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.35	6.65	0.250	0.262
D1	5.20	5.40	0.205	0.213
E	5.40	5.70	0.213	0.224
e	2.20	2.40	0.087	0.094
e1	4.40	4.80	0.173	0.189
L	10.00	11.00	0.393	0.433
L1	2.70	3.10	0.106	0.122
L2	1.40	1.80	0.055	0.071
L3	0.90	1.50	0.035	0.059

## Disclaimer

The information presented in this document is for reference only. Guangdong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.